P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 12	0.032 at V_{GS} = - 4.5 V	- 5.3
	0.042 at V_{GS} = - 2.5 V	- 4.6
	0.059 at V_{GS} = - 1.8 V	- 3.9

FEATURES

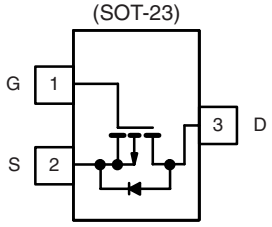
- **Halogen-free According to IEC 61249-2-21 Available**
- TrenchFET® Power MOSFET

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

- Load Switch
- PA Switch

TO-236
(SOT-23)



Top View

Si2333DS (E3)*

* Marking Code

Ordering Information: Si2333DS-T1-E3 (Lead (Pb)-free)
Si2333DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**5 s**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	- 12		V
Gate-Source Voltage		V_{GS}	± 8		
Continuous Drain Current (T_J = 150 °C)[a, b]	T_A = 25 °C	I_D	- 5.3	- 4.1	A
	T_A = 70 °C		- 4.2	- 3.3	
Pulsed Drain Current		I_{DM}	- 20		
Continuous Source Current (Diode Conduction)[a, b]		I_S	- 1.0	- 0.6	
Maximum Power Dissipation[a, b]	T_A = 25 °C	P_D	1.25	0.75	W
	T_A = 70 °C		0.8	0.48	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 5 s	R_{thJA}	75	100	°C/W
	Steady State		120	166	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	40	50	

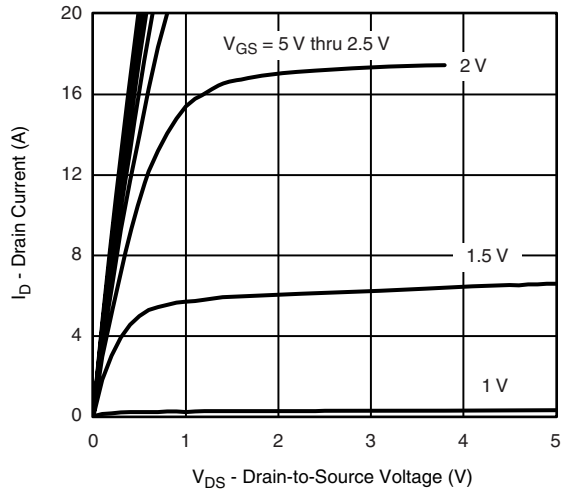
Notes:
a. Surface Mounted on 1" x 1" FR4 board.
b. Pulse width limited by maximum junction temperature.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
			Limits			
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = - 250 µA	- 12			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 0.40		- 1.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 9.6 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 9.6 V, V_{GS} = 0 V, T_J = 55 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 20			A
Drain-Source On-Resistance[a]	$R_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 5.3 A		0.025	0.032	Ω
		V_{GS} = - 2.5 V, I_D = - 4.6 A		0.033	0.042	
		V_{GS} = - 1.8 V, I_D = - 2.0 A		0.046	0.059	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 5 V, I_D = - 5.3 A		17		S
Diode Forward Voltage	V_{SD}	I_S = - 1.0 A, V_{GS} = 0 V		- 0.7	- 1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = - 6 V, V_{GS} = - 4.5 V $I_D \cong$ - 5.3 A		11.5	18	nC
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			3.2		
Input Capacitance	C_{iss}	V_{DS} = - 6 V, V_{GS} = 0 V, f = 1 MHz		1100		pF
Output Capacitance	C_{oss}			390		
Reverse Transfer Capacitance	C_{rss}			300		
Switching[c]						
Turn-On Time	$t_{d(on)}$	V_{DD} = - 6 V, R_L = 6 Ω $I_D \cong$ - 1.0 A, V_{GEN} = - 4.5 V R_G = 6 Ω		25	40	ns
	t_r			45	70	
Turn-Off Time	$t_{d(off)}$			72	110	
	t_f			60	90	

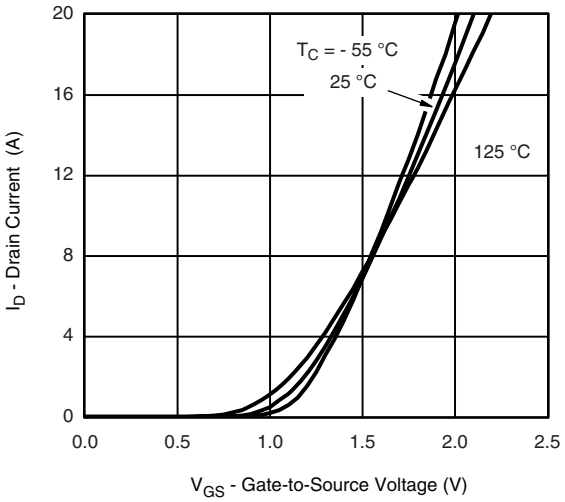
Notes:
a. Pulse test: PW ≤ 300 µs, duty cycle ≤ 2 %.
b. For design aid only, not subject to production testing.
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

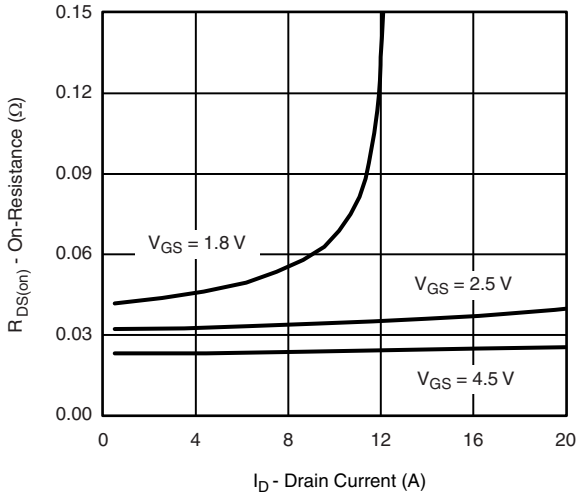
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



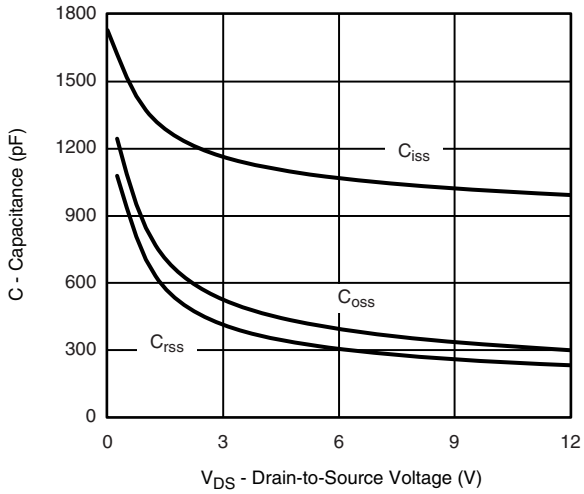
Output Characteristics



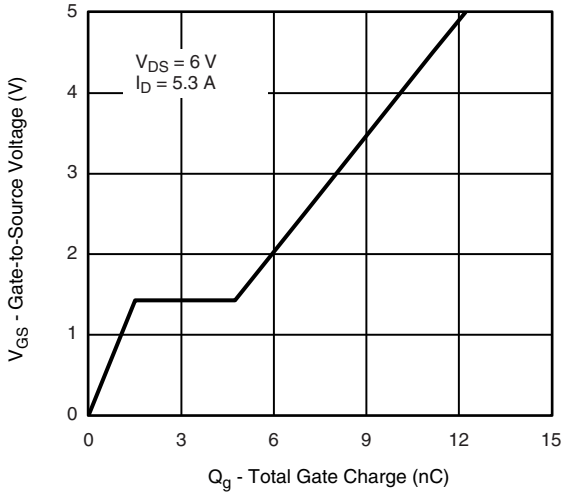
Transfer Characteristics



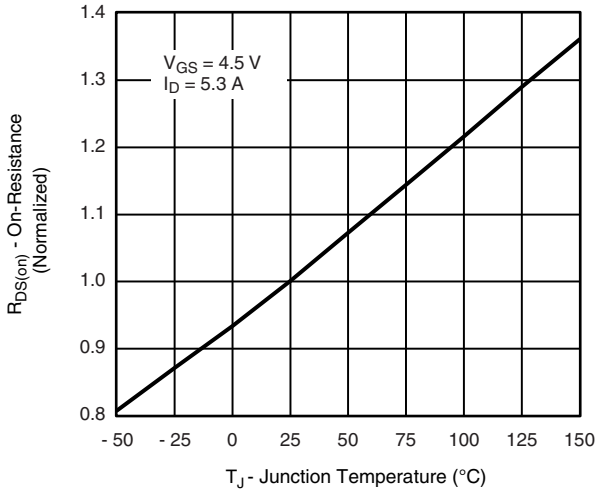
On-Resistance vs. Drain Current



Capacitance

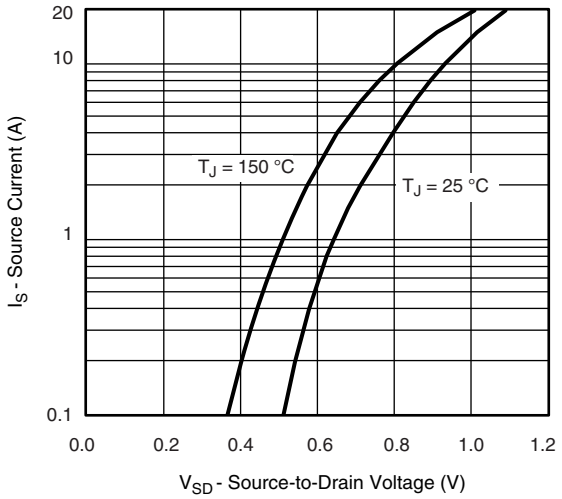


Gate Charge

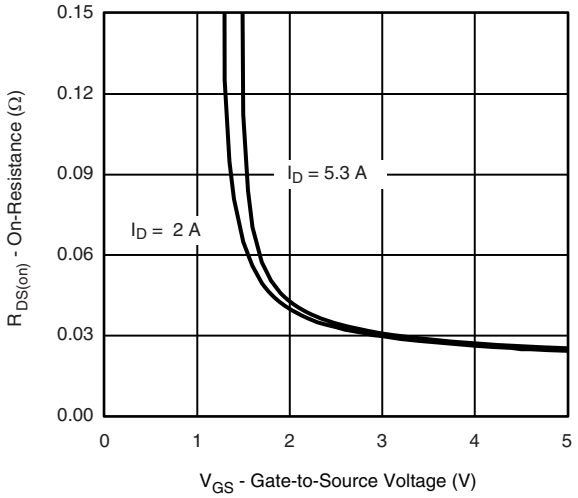


On-Resistance vs. Junction Temperature

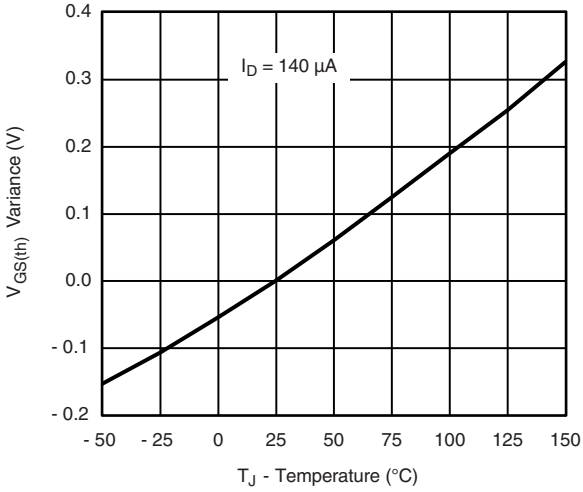
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



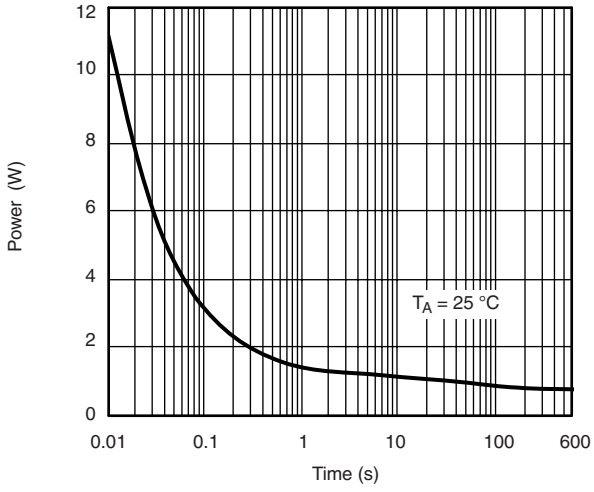
Source-Drain Diode Forward Voltage



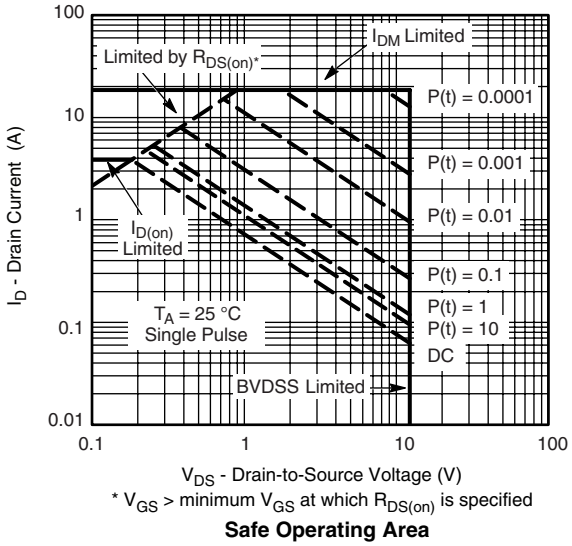
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



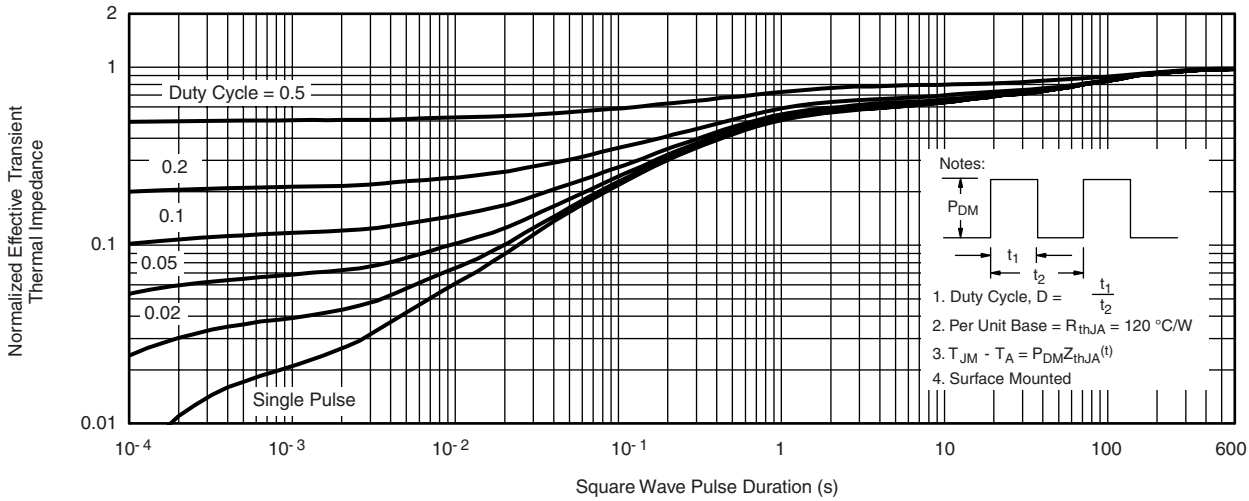
Single Pulse Power



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

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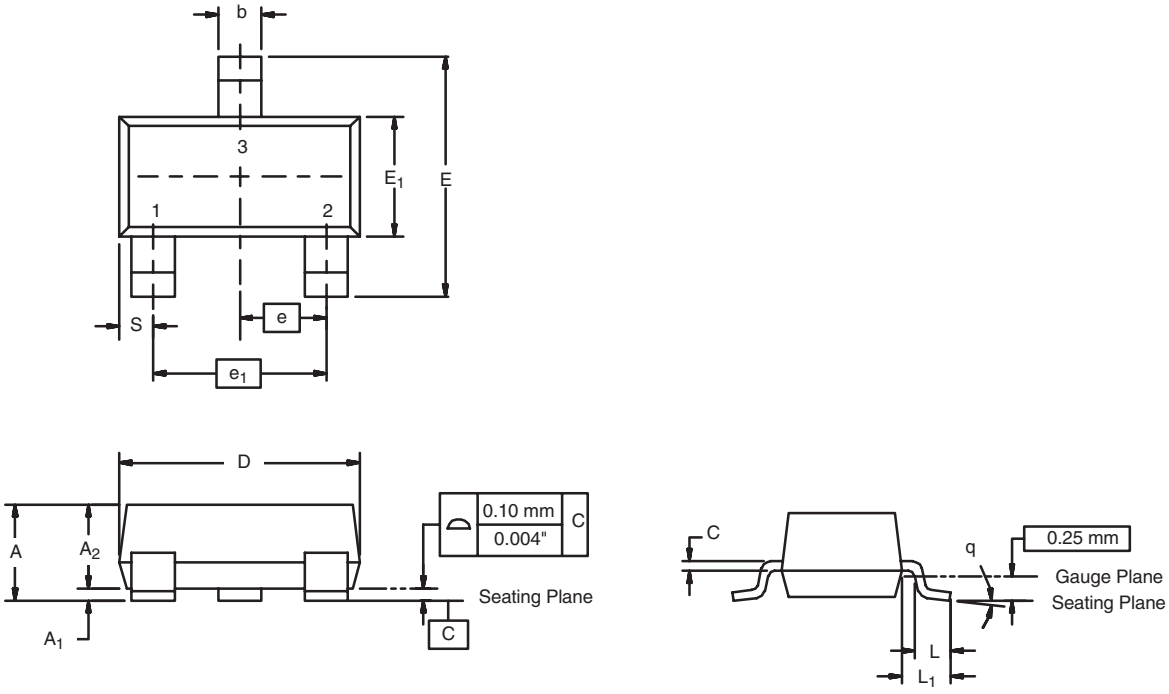
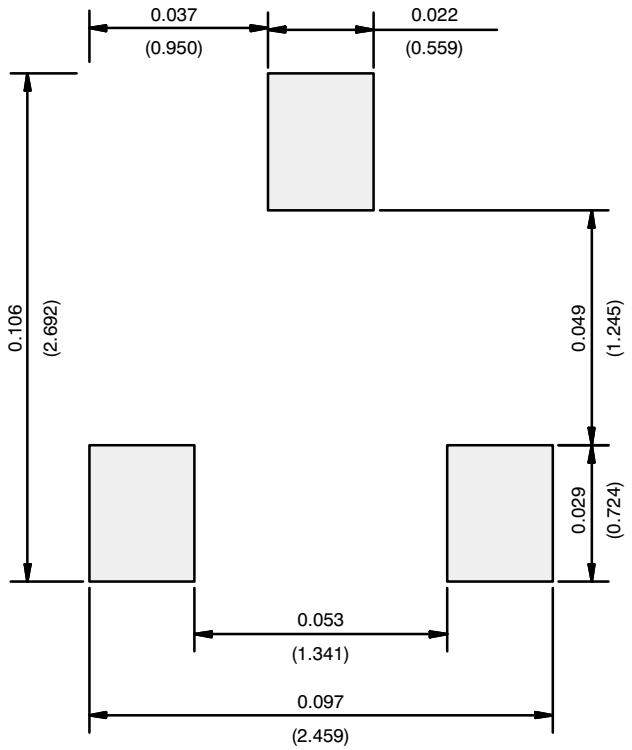
SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A_1	0.01	0.10	0.0004	0.004
A_2	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E_1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e_1	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L_1	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01 DWG: 5479				

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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